

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

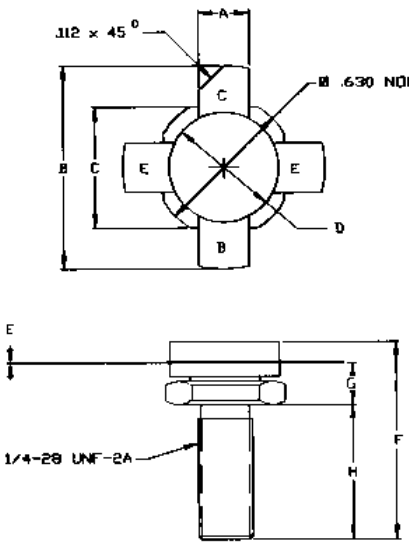
The **ASI TPV376** is a Common Emitter Device Designed for High Linearity Class A Television Band III (170-230 MHz) Applications.

FEATURES INCLUDE:

- Gold Metalization
- Emitter Ballasting

MAXIMUM RATINGS

I_C	16 A
V_{CB}	60 V
P_{DISS}	150 W @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+150^\circ C$
θ_{JC}	$1.2^\circ C/W$

PACKAGE STYLE .550 4L STUD(1/4)		
	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.220/5.59	.230/5.84
B		1.050/26.67
C	.545/13.84	.555/14.10
D	.495/12.57	.505/12.83
E	.003/0.08	.007/0.18
F		.830/21.08
G	.185/4.70	.198/5.03
H	.497/12.62	.530/13.46

CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 100 mA			30			V
BV_{CER}	I _C = 100 mA	R _{BE} = 10 Ω		60			V
BV_{CBO}	I _C = 100 mA			60			V
BV_{EBO}	I _E = 20 mA			4.0			V
h_{FE}	V _{CE} = 5.0 V	I _C = 1.0 A		10		120	---
C_{ob}	V _{CB} = 30 V						



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